

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9. (Canceled)

10. (Currently Amended) A method for producing a single crystal by Czochralski method by pulling a seed crystal from a raw material melt, comprising:

immersing a seed crystal into a raw material melt; and

growing a single crystal by rotating and pulling the seed crystal,

~~wherein~~ wherein:

the single crystal is pulled with controlling a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$)

within a determined range; ~~and range~~;

the range of a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$), including a desired defect region and/or a desired defect-free region, is determined according to T_{max} ($^{\circ}\text{C}$); ~~T_{max} ($^{\circ}\text{C}$)~~;

wherein:

V (mm/min) is the single crystal pulling rate of pulling a single crystal;

G (K/mm) is a temperature gradient at a solid-liquid interface, in a range of ~~the~~ a melting point of the raw material and 1400°C ; ~~and~~

T_{max} ($^{\circ}\text{C}$) is the highest temperature of the raw material melt at an interface between a quartz crucible inner wall and a raw material ~~melt~~ melt; ~~and~~

the range of a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) is selected from a group consisting of:

from $-0.000724 [\text{mm}^2/(\text{^{\circ}\text{C}} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{^{\circ}\text{C}}) + 1.31$
 $(\text{mm}^2/\text{K} \cdot \text{min})$ to less than $-0.000724 [\text{mm}^2/(\text{^{\circ}\text{C}} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{^{\circ}\text{C}}) + 1.38$

$(\text{mm}^2/\text{K} \cdot \text{min})$;

$$\underline{-0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.38}$$

(mm²/K • min) or more; and

$$\underline{\text{from } -0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.31}$$

(mm²/K • min) to $-0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.35 (\text{mm}^2/\text{K} \cdot \text{min})$.

11-13. (Canceled)

14. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the $T_{\text{max}} (\text{°C})$ being in a range of 1560 °C or less.

15-17. (Canceled)

18. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein, at least, the $T_{\text{max}} (\text{°C})$ is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19-21. (Canceled)

22. (Previously Presented) The method for producing a single crystal according to Claim 14, wherein, at least, the $T_{\text{max}} (\text{°C})$ is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23-25. (Canceled)

26. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein a silicon single crystal is pulled as the single crystal.

27. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein a single crystal with a diameter of 200mm or more is pulled as the single crystal.

28. (Canceled)